Description

The GM76V256C family is a 262,144 bits static random access memory organized as 32,768 words by 8 bits. Using a 0.6*u*m advanced CMOS tech-nology and operated a single 3.3V supply.

Advanced circuit techniques provide both high speed and low power consumption. The Family can support various operating temerature ranges for user flexibility of system design.

The Family has Chip select /CS, which allows for device selection and data retention control, and output enable (/OE), which provides fast memory access. Thus it is suitable for high speed and low power applications, particularly where battery back-up is required.

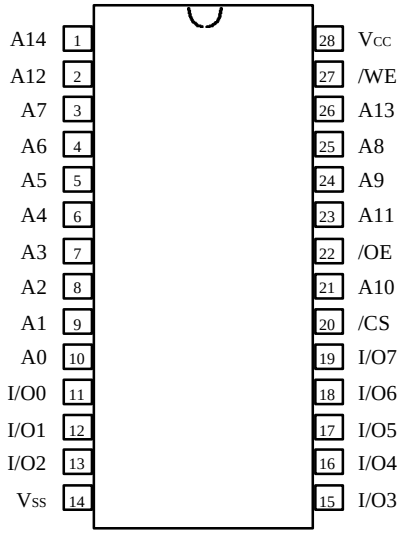
Features

* High Speed : Fast Access and Cycle Time
  85/100ns Max
* Low Power Standby and Low Power Operation
  -Standby : 54uW at T_A= -25 ~ 85℃ (LLE)
  36uW at T_A= 0 ~ 70℃ (LL)
  -Operation : 126mW at Vcc=3.3V ± 0.3V
* Completely Static RAM : No Clock or Timing strobe required
* Power Supply Voltage : 3.3V ± 0.3V
* Low Data Retention Voltage : 2.0V(Min)
* Temperature Range
  -GM76V256CL/LL : (0 ~ 70℃)
  -GM76V256CLE/LLE : (-25 ~ 85℃)
* Package Type : JEDEC Standard 28-SOP,TSOP(I)

Pin Description

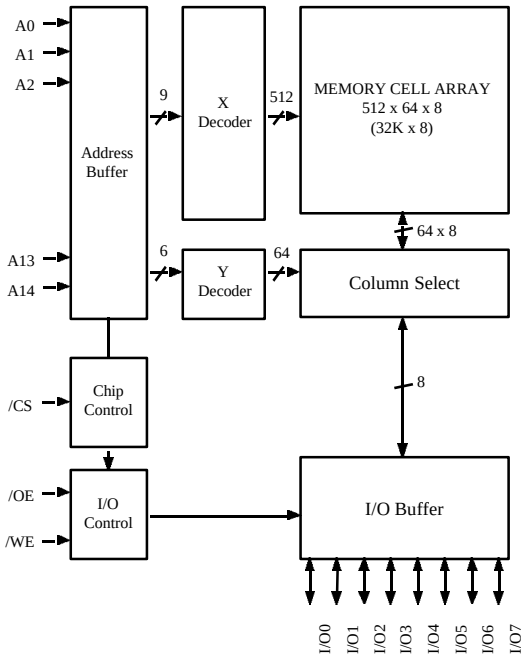
Pin	Function
A0-A14	Address Inputs
/WE	Write Enable Input
/OE	Output Enable Input
/CS	Chip Select Input
I/O0-I/O7	Data Input/Output
V_{CC}	Power Supply
V_{SS}	Ground

Pin Configuration



(Top View)

Block Diagram



Absolute Maximum Ratings [*1]

Symbol	Parameter		Rating	Unit
T_A	Ambient Temperature under Bias	GM76V256CL/LL	0 ~ 70	C
		GM76V256CLE/LLE	-25 ~ 85	C
T_{STG}	Storage Temperature		-65 ~ 150	C
V_{SOL}	Soldering Temperature and Time		260, 10 (at lead)	C,S
V_{CC}	Supply Voltage		-0.3 ~ 4.6	V
V_{IN}	Input Voltage		-0.3[*2]~ 4.6	V
$V_{I/O}$	Input and Output Voltage		-0.5 ~ V_{CC} + 0.5	V
P_D	Power Dissipation		1.0	W

Notes:
1. Operation at above Absolute Maximum Ratings can adversely affect device reliability.
2. -3.0V at pulse width 50ns Max.

Recommended DC Operating Conditions (T_A = -25 ~ 85C)

Symbol	Parameter	GM76V256C			Unit
		Min	Typ	Max	
V_{CC}	Supply Voltage	3.0	3.3	3.6	V
V_{IH}	Input High Voltage	2.2	-	V_{CC} + 0.3	V
V_{IL}	Input Low Voltage	-0.3*	-	0.4	V

*Note: V_{IL}=-3.0V Min for pulse width less than 50ns.

Truth Table

/CS	/WE	/OE	Input/Output	MODE
H	X	X	Hi-Z	Not Selected
L	H	L	Output Data	Read
L	L	X	Input Data	Write
L	H	H	Hi-Z	Output Disable

*Note: X means "don't care".

DC Electrical Characteristics (V_{CC}=3.3V $\pm$ 0.3V , T_A = -25 ~ 85℃)

Symbol	Parameter	Test Conditions		GM76V256C			Unit
				Min	Typ	Max	
$I_{I(L)}$	Input Leakage Current	V_{IN} = 0 to V_{CC}		-1	-	1	uA
$I_{O(L)}$	Output Leakage Current	/CS = V_{IH} or /OE = V_{IH} or WE = V_{IL}, V$\leq$ V_{OUT} $\leq$ V_{CC}		-1	-	1	uA
V_{OH}	High Level Output Voltage	I_{OH} = -1.0mA		2.4	-	-	V
V_{OL}	Low Level Output Voltage	I_{OL} = 2.1mA		-	-	0.4	V
I_{CC}	Operating Supply Current	/CS = V_{IL}, V_{IN} = V_{IH}/V_{IL}, $I_{I/O}$ = 0mA		-	-	2	mA
I_{CC1}	Average Operating Current	/CS = V_{IL}, V_{IN} = V_{IH}/V_{IL} $I_{I/O}$ = 0mA tcycle = Min, cycle		-	-	35	mA
I_{CC2}	Average Operating Current	/CS = V_{IL}, V_{IN} = V_{IH}/V_{IL} $I_{I/O}$ = 0mA tcycle = 1us, cycle		-	-	5	mA
I_{CCS1}	Standby Current (TTL)	/CS = V_{IH}		-	-	0.5	mA
I_{CCS2}	Standby Current (CMOS)	/CS $\leq$ V_{CC}-0.2V(LL)	0 to +70℃ (LL)	-	-	10	uA
			-25 to +85℃ (LLE)	-	-	15	uA
		/CS $\leq$ V_{CC}-0.2V (L)	0 to +70℃ (L)	-	-	20	uA
			-25 to +85℃ (LE)	-	-	30	uA

*TYP. Values are measured at 25℃, V_{CC} = 3.3V

AC Operating Characteristics (V_{CC}=3.3V ± 0.3V , T_A = -25 ~ 85℃)

Read Cycle

Symbol	Parameter	Condi-tions	GM76V256C-85		GM76V256C-10		Unit
			Min	Max	Min	Max	
t_{RC}	Read Cycle Time	*1	85	-	100	-	ns
t_{AA}	Address Access Time		-	85	-	100	ns
t_{ACS}	Chip Select Access Time		-	85	-	100	ns
t_{OE}	Output Enable Access Time		-	45	-	50	ns
t_{OH}	Output Hold Time		10	-	15	-	ns
t_{CLZ}	Chip Select Output Setup Time	*2	10	-	10	-	ns
t_{OLZ}	Output Enable Output Setup Time		5	-	5	-	ns
t_{CHZ}	Chip Select Output Floating		0	30	0	35	ns
t_{OHZ}	Output Enable Output Floating		0	30	0	35	ns

Write Cycle

Symbol	Parameter	Condi-tions	GM76V256C-85		GM76V256C-10		Unit
			Min	Max	Min	Max	
t_{WC}	Write Cycle Time	*1	85	-	100	-	ns
t_{CW}	Chip Select Time		75	-	80	-	ns
t_{AW}	Address Enable Time		70	-	80	-	ns
t_{AS}	Address Set-up Time		0	-	0	-	ns
t_{WP}	Write Pulse Width		60	-	70	-	ns
t_{WR}	Address Hold Time		0	-	0	-	ns
t_{DW}	Input Data Setup Time		35	-	40	-	ns
t_{DH}	Input Data Hold Time		0	-	0	-	ns
t_{WHZ}	Write to Output in High-Z	*2	0	30	0	30	ns
t_{OW}	Output Active from End of Write		5	-	10	-	ns

***1 Test Conditions.**

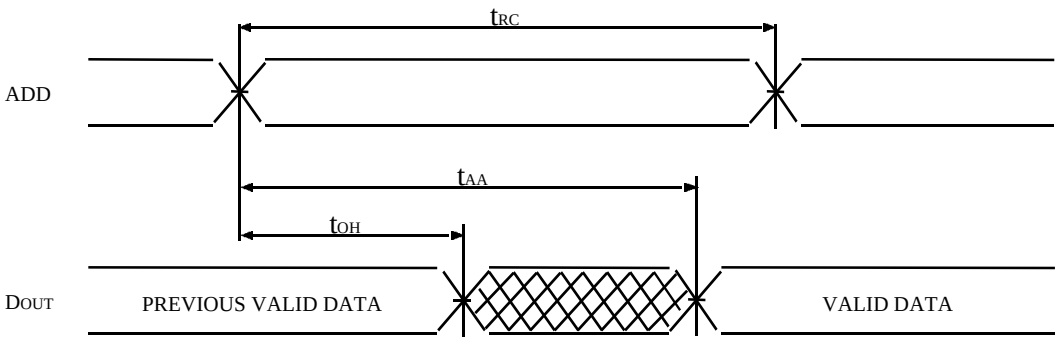
1. Input pulse level : 0.4V to 2.2V
2. tr = tf = 5ns
3. Input/output timing reference level : 1.5V
4. Output load C_L = 100pF + 1TTL Load

***2 Test Conditions.**

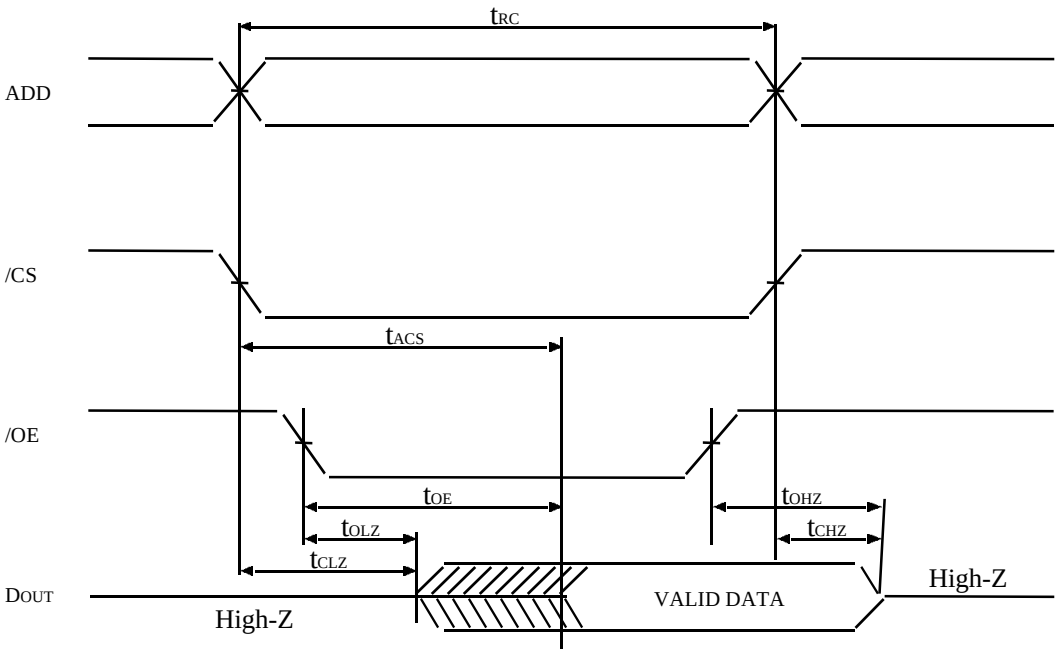
1. Input pulse level : 0.4V to 2.2V
2. tr = tf = 5ns
3. Input timing reference level : 1.5V
4. Output timing reference level : +/-200mV (the level displacement from stable output voltage level)
5. Output load C_L = 5pF + 1TTL Load

Timing Waveforms

Read Cycle 1 (Note 1, 2)

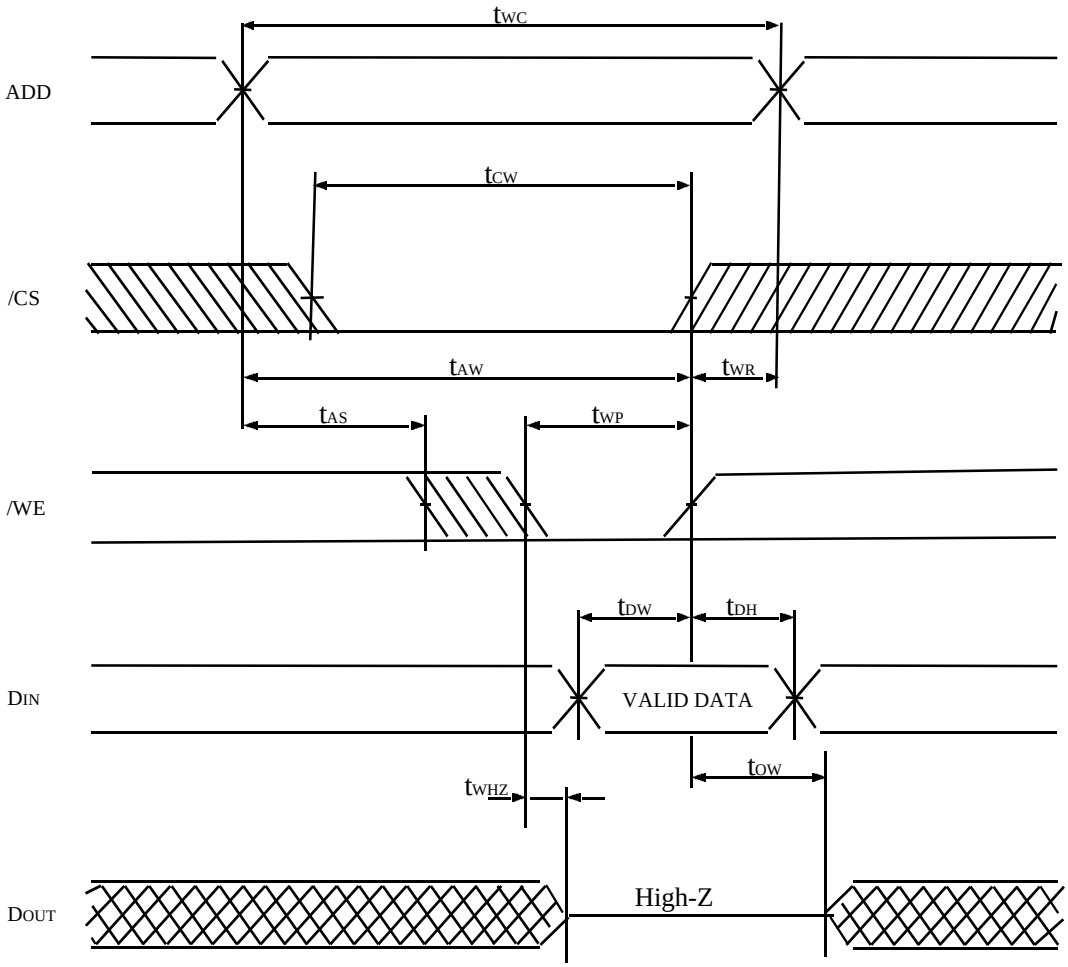


Read Cycle 2 (Note 2)



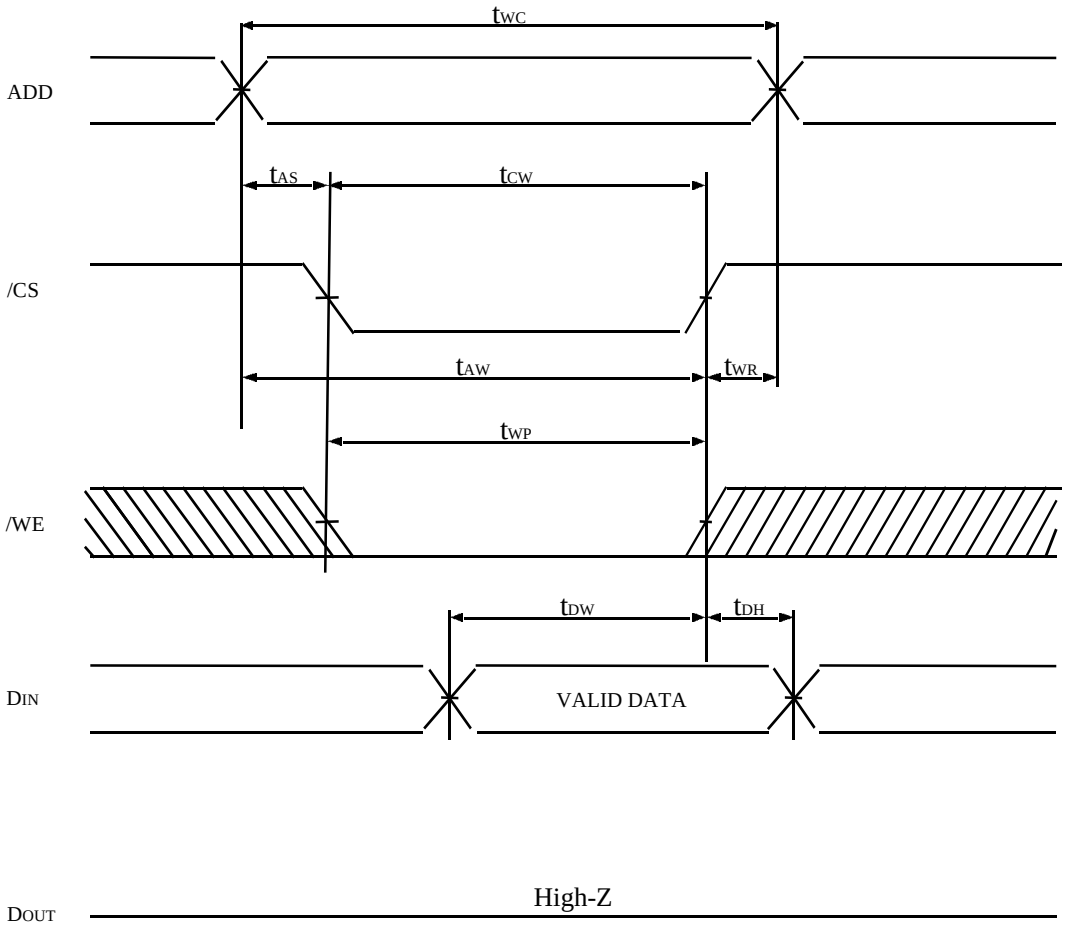
Notes:
1. Device is continuously selected. /OE, /CS $\leq$ $V_{IL.}$
2. /WE is high for read cycle.

Write Cycle 1 (/WE Controlled) (Note 1, 2)



Notes:
1. The internal write time of the memory is defined by the overlap of /CS low and /WE low. Both signals must be low to initiate a write and either signal can terminate a write by going high. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
2. Data I/O is high impedance if /OE = V_{IH}.

Write Cycle 2 (/CS Controlled) (Note 1, 2, 3)



Notes:
1. The internal write time of the memory is defined by the overlap of /CS low and /WE low. Both signals must be low to initiate a write and either signal can terminate a write by going high. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
2. Data I/O is high impedance if /OE = V_{IH}.
3. If /CS goes high simultaneously with /WE high, the output remains in a high impedance state.

Capacitance (f = 1MHz, T_A = 25℃)

Symbol	Parameter	Test Conditions	Min	Max	Unit
C_{IN}	Input Capacitance	V_I = 0V	-	6	pF
C_{OUT}	Output Capacitance	V_O = 0V	-	8	pF

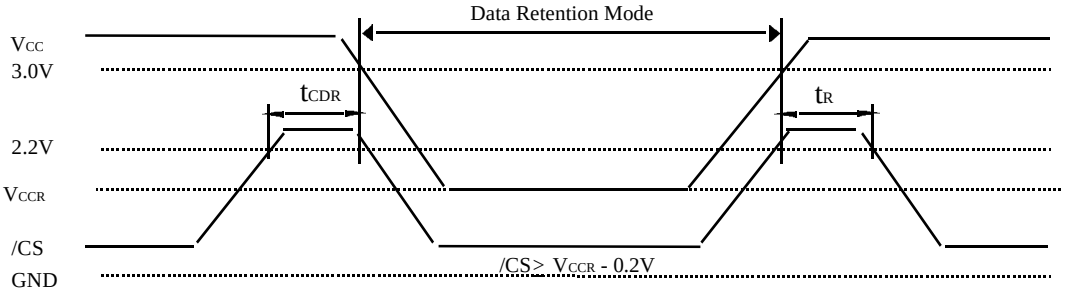
*Note: This parameter is sampled and not 100% tested.

Data Retention Characteristics (T_A = -25 ~ 85℃)

Symbol	Parameter		Test Conditions	Min	Typ	Max	Unit
V_{CCR}	Data Retention Supply Voltage		/CS ≥ V_{CCR} - 0.2V	2.0	-	3.6	V
I_{CCR}	Data Retention Current	0 to +70℃ (LL)	V_{CC} = 3.0V /CS ≥ 2.8V	-	0.5 *1	7	uA
		-25 to +85℃ (LLE)		-	0.5 *1	10	
		0 to +70℃ (L)		-	1 *1	15	
		-25 to +85℃ (LE)		-	1 *1	20	
t_{CDR}	Chip Select to Data Retention Time		Refer to the figure below	0	-	-	ns
t_R	Operation Recovery Time			t_{RC} *2	-	-	ns

Notes:
1. Typ, Values are measured at 25℃
2. Read Cycle Time

Data Retention Timing

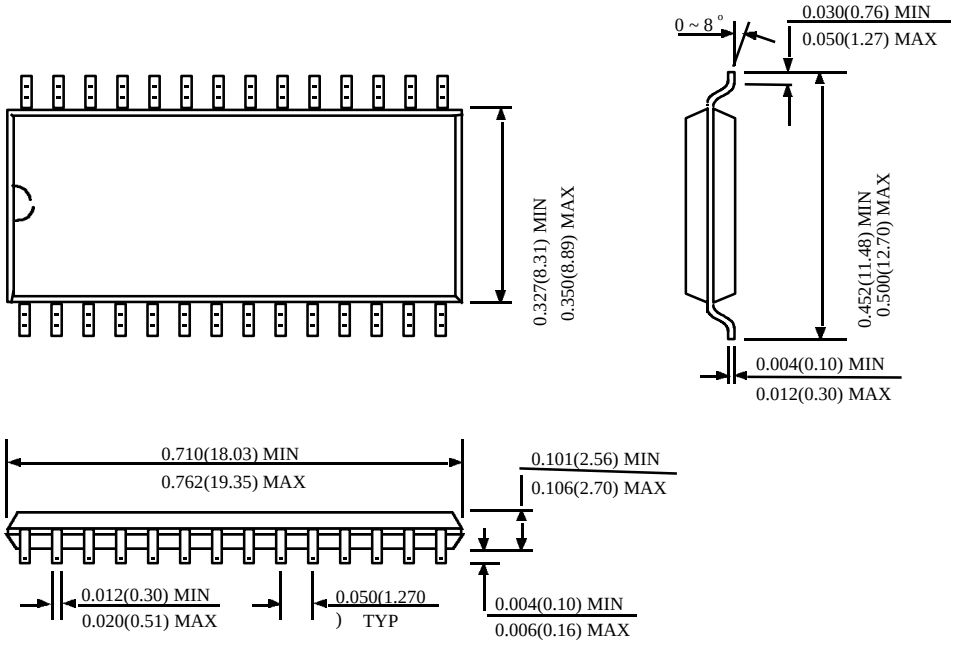


Note: When retaining data in standby mode, supply voltage can be lowered within a certain range.
Read or write cycle cannot be performed while the supply voltage is low.

Package Dimensions

Unit: Inches (mm)

28 SOP



Unit: Inches (mm)

28 TSOP-I